October 1987 Revised January 2004

CD4023BC Buffered Triple 3-Input NAND Gate

General Description

FAIRCHILD

SEMICONDUCTOR

These triple gates are monolithic complementary MOS (CMOS) integrated circuits constructed with N- and P-channel enhancement mode transistors. They have equal source and sink current capabilities and conform to standard B series output drive. The devices also have buffered outputs which improve transfer characteristics by providing very high gain. All inputs are protected against static discharge with diodes to V_{DD} and V_{SS} .

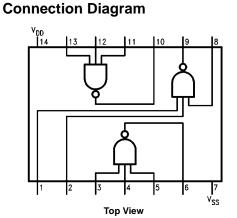
Features

- Wide supply voltage range: 3.0V to 15V
- High noise immunity: 0.45 V_{DD} (typ)
- Low power TTL compatibility:
- fan out of 2 driving 74L or 1 driving 74LS ■ 5V–10V–15V parametric ratings
- Symmetrical output characteristics
- Maximum input leakage 1 µA at 15V over full temperature range

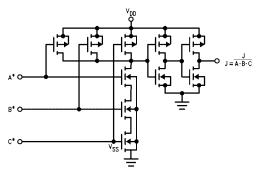
Ordering Code:

Order Number	Package Number	Package Description
CD4023BCM (Note 1)	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
CD4023BCSJ	M14D	14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
CD4023BCN	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide

Note 1: Devices also available in Tape and Reel. Specify by appending the suffix letter "X" tot he ordering code.



Block Diagram



1/3 Device Shown

*All Inputs Protected by Standard CMOS Input Protection Circuit.

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Absolute Maximum Ratings(Note 2) (Note 3)

DC Supply Voltage (V _{DD})	–0.5 V_{DC} to +18 V_{DC}
Input Voltage (V _{IN})	–0.5 V_{DC} to $V_{DD} \mbox{+} 0.5$ V_{DC}
Storage Temp. Range (T _S)	-65°C to +150°C
Power Dissipation (P _D)	
Dual-In-Line	700 mW
Small Outline	500 mW
Lead Temperature (TL)	
(Soldering, 10 seconds)	260°C

DC Electrical Characteristics (Note 4)

Recommended Operating Conditions

DC Supply Voltage (V_{DD}) Input Voltage (V_{IN}) Operating Temperature Range (T_A) 5 V_{DC} to 15 V_{DC} 0 V_{DC} to V_{DD} V_{DC} -55°C to +125°C

Note 2: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed; they are not meant to imply that the devices should be operated at these limits. The table of "Recommended Operating Conditions" and "Electrical Characteristics" provides conditions for actual device operation.

Note 3: $V_{SS} = 0V$ unless otherwise specified.

-55°C +25°C +125°C Symbol Conditions Units Parameter Min Min Max Min Max Тур Тур Quiescent Device Current $V_{DD} = 5V$ 0.25 0.004 0.25 I_{DD} 7.5 $V_{DD} = 10V$ 0.5 0.005 0.5 15 μΑ $V_{DD} = 15V$ 1.0 0.006 1.0 30 0.05 VOL LOW Level Output Voltage $V_{DD} = 5V$ 0.05 0.05 0 $V_{DD} = 10V$ 0.05 0 0.05 0.05 v $V_{DD} = 15V$ 0.05 0 0.05 0.05 VOH HIGH Level Output Voltage $V_{DD} = 5V$ 4.95 4.95 5 4.95 9.95 V $V_{DD} = 10V$ 9.95 9.95 10 $V_{DD} = 15V$ 14.95 14.95 15 14.95 V_{IL} LOW Level Input Voltage V_{DD}=5V, V_O=4.5V 2 1.5 1.5 1.5 V_{DD}=10V, V_O=9.0V 3.0 4 3.0 3.0 V |I_O|<1μA V_{DD}=15V, V_O=13.5V 4.0 6 4.0 4.0 V_{IH} HIGH Level Input Voltage V_{DD}=5V, V_O=0.5V 3.5 3.5 3 3.5 V_{DD}=10V, V_O=1.0V V $|I_0|{<}1\mu A$ 7.0 7.0 6 7.0 V_{DD}=15V, V_O=1.5V 11.0 11.0 9 11.0 LOW Level Output Current V_{DD}=5V, V_O = 0.4V 0.64 0.51 0.88 0.36 IOL (Note 5) $V_{DD} = 10V, V_O = 0.5V$ 1.6 1.3 2.2 0.90 mΑ V_{DD} = 15V, V_O = 1.5V 2.4 42 34 8 HIGH Level Output Current $V_{DD} = 5V, V_O = 4.6V$ -0.64 -0.88 I_{OH} -0.51 -0.36 (Note 5) V_{DD} = 10V, V_O = 9.5V -2.2 -0.90 mA -1.6 -1.3 $V_{DD} = 15V, V_{O} = 13.5V$ -4.2 -3.4 -8 -2.4 $V_{DD} = 15V, V_{IN} = 0V$ I_{IN} Input Current -0.1 10 -0.1 -1.0 μΑ $V_{DD} = 15V, V_{IN} = 15V$ 0.1 10⁻⁵ 0.1 1.0

Note 4: $V_{SS} = 0V$ unless otherwise specified.

Note 5: I_{OH} and I_{OL} are tested one output at a time.

$T_A = 25^{\circ}C$, $C_L = 50$ pF, $R_L = 200$ k, unless otherwise specified							
Symbol	Parameter	Conditions	Min	Тур	Max	Units	
t _{PHL} Pr	Propagation Delay, HIGH-to-LOW Level	$V_{DD} = 5V$		130	250		
		$V_{DD} = 10V$		60	100	ns	
		$V_{DD} = 15V$		40	70		
t _{PLH} Pro	Propagation Delay, LOW-to-HIGH Level	$V_{DD} = 5V$		110	250		
		$V_{DD} = 10V$		50	100	ns	
		$V_{DD} = 15V$		35	70		
t _{THL} ,	Transition Time	$V_{DD} = 5V$		90	200		
t _{TLH}		$V_{DD} = 10V$		50	100	ns	
		$V_{DD} = 15V$		40	80		
C _{IN}	Average Input Capacitance	Any Input		5	7.5	pF	
CPD	Power Dissipation Capacity (Note 7)	Any Gate		17		pF	

Note 6: AC Parameters are guaranteed by DC correlated testing.

Note 7: C_{PD} determines the no load AC power consumption of any CMOS device. For complete explanation, see Family Characteristics Application Note AN-90.

